WEST Search History for Application 10597432

Creation Date: 2008102709:45

Query	DB	Op.	Plur.	Thes.	Date
("20010044180" |"20030022457" |"4877750" |"5776628" |"6020234" |"6057188" |"6150210" |"6190988" |"6204112" |"6319788" |"6326261").PN.	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		10-26-2008
(trench same capacitor)	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		10-27-2008
((trench same capacitor)) and (DRAM or dynamic random access memory)	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		10-27-2008
((trench same capacitor) and (DRAM or dynamic random access memory)) and (plate near4 (connect$ or contact))	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		10-27-2008
((trench same capacitor) and (DRAM or dynamic random access memory) and (plate near4 (connect$ or contact))) and ((third or three) near3 (dielectric or insulat$))	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		10-27-2008
((trench same capacitor) and (DRAM or dynamic random access memory) and (plate near4 (connect$ or contact))) and ((third or three) near3 (dielectric or insulat$) same (storage or plate))	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		10-27-2008
((trench same capacitor) and (DRAM or dynamic random access memory) and (plate near4 (connect$ or contact))) and ((third or three) near3 (dielectric or insulat$) same (storage or plate)).clm.	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		10-27-2008
((trench same capacitor) and (DRAM or dynamic random access memory) and (plate near4 (connect$ or contact)) and ((third or three) near3 (dielectric or insulat$) same (storage or plate))) and (dopant or implant$)	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		10-27-2008
"thomas" near3 "dyer".inv.	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		10-27-2008

("thomas" near3 "dyer".inv.) and ((trench same capacitor) and (DRAM or dynamic random access memory) and (plate near4 (connect$ or contact)) and ((third or three) near3 (dielectric or insulat$)))	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		10-27-2008
"carl" near2 "radens".inv.	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		10-27-2008
("carl" near2 "radens".inv.) and ((trench same capacitor) and (DRAM or dynamic random access memory) and (plate near4 (connect$ or contact)) and ((third or three) near3 (dielectric or insulat$)))	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		10-27-2008